



Pin 2 – back side – GND

**Mechanical data:**  $A_x= 1000 \mu\text{m}$ ,  $A_y=600\mu\text{m}$

Pad Size for Pin 1, 3, 4, 6 -  $85*95 \mu\text{m}$

Pad Size for Pin 5 -  $270*105 \mu\text{m}$

**Chip thickness:**  $138\pm 12\mu\text{m}$

**Scribe Line width** -  $60\mu\text{m}$

**Top Metal:** Al - for wire bonding

**Back side - Anode:** Ti-Ni-Ag for soldering

**Sample testing:** no bad dice inking;  
 guaranteed good dice quantity  $\geq 93\%$

**Schematic and pinning diagram**

### Limiting values

Parameter	Symbol	Conditions	Value	Unit
Peak Pulse Power	$P_{pp}$	$t_p=8/20\mu\text{s}$	-	W
Peak Pulse Current	$I_{pp}$	$t_p=8/20\mu\text{s}$ ; Any I/O to Pin5; Pin2 to Any I/O	25*	A
Electrostatic Discharge	$V_{ESD}$	IEC 61000-4-2. Any I/O to Pin5; Pin2 to Any I/O	+30 (Contact); +30 (Air).	kV
Max.junction temperature	$T_j$	-	+125	$^{\circ}\text{C}$

### Characteristics (Ta=25°C)

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Reverse Stand-off voltage	$V_{RWM}$	-	-	-	3,3	V
Breakdown voltage	$V_{BR}$	$I_R=1mA$ . Pin 5 to Pin 2.	5,0	-	-	V
Reverse leakage current	$I_R$	$V=+3,5V$ . Any I/O to Pin 2. $V=-3,5V$ . Any I/O to Pin 5.	-	-	0,5	$\mu A$
Forward Voltage	$V_F$	$I_f=15mA$ . Pin 2 to Any I/O & Any I/O to Pin5	-	-	1,0	V
Forward Voltage	$V_{CL}$	$I_{pp}=1.0A$ , $t_p=8/20\mu s$ $I_{pp}=10.0A$ , $t_p=8/20\mu s$ $I_{pp}=25.0A$ , $t_p=8/20\mu s$ ; Any I/O to Pin 5	-	-	1,0* 3,7* 8,2*	V
Capacitance. Any I/O pin to Ground	$C_J$	$V_R=0V$ , $f=1MHz$	-	-	5,0	pF
Capacitance. Any I/O pin to I/O	$C_J$	$V_R=0V$ , $f=1MHz$	-	-	2,5	pF

\*- For Device testing